



ALPHA & OMEGA
SEMICONDUCTOR

AOD424

20V N-Channel MOSFET

General Description

The AOD424 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Product Summary

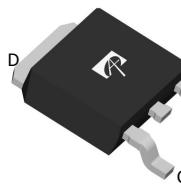
V_{DS}	20V
I_D (at $V_{GS}=4.5V$)	45A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 4.4mΩ
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	< 5.7mΩ

100% UIS Tested
100% R_g Tested

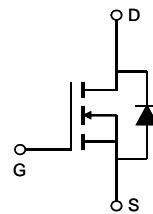
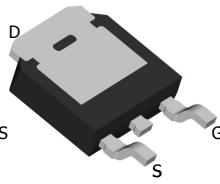


**TO252
DPAK**

Top View



Bottom View



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^G	I_D	45	A
$T_C=100^\circ\text{C}$		35	
Pulsed Drain Current ^C	I_{DM}	160	
Continuous Drain Current	I_{DSM}	18	A
$T_A=70^\circ\text{C}$		15	
Avalanche Current ^C	I_{AS}, I_{AR}	57	A
Avalanche energy L=0.1mH ^C	E_{AS}, E_{AR}	162	mJ
Power Dissipation ^B	P_D	100	W
$T_C=100^\circ\text{C}$		50	
Power Dissipation ^A	P_{DSM}	2.5	W
$T_A=70^\circ\text{C}$		1.6	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{θJA}$	16	20	°C/W
Maximum Junction-to-Ambient ^{A,D}		41	50	°C/W
Maximum Junction-to-Case	$R_{θJC}$	1.2	1.5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$			100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.5	1	1.6	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	160			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}, I_D=20\text{A}$ $T_J=125^\circ\text{C}$		3.6 5.1	4.4 6.2	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}, I_D=20\text{A}$		4.5	5.7	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$		105		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.7	1	V
I_S	Maximum Body-Diode Continuous Current ^G				45	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$	3080	3860	4630	pF
C_{oss}	Output Capacitance		520	740	960	pF
C_{rss}	Reverse Transfer Capacitance		350	580	810	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	0.6	1.4	2.1	Ω
SWITCHING PARAMETERS						
$Q_g(4.5\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=10\text{V}, I_D=20\text{A}$	28	36	43	nC
Q_{gs}	Gate Source Charge			9		nC
Q_{gd}	Gate Drain Charge			12		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=10\text{V}, R_L=0.5\Omega, R_{\text{GEN}}=3\Omega$		7		ns
t_r	Turn-On Rise Time			8		ns
$t_{\text{D(off)}}$	Turn-Off Delay Time			70		ns
t_f	Turn-Off Fall Time			18		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	13	17	20	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	29	36	43	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

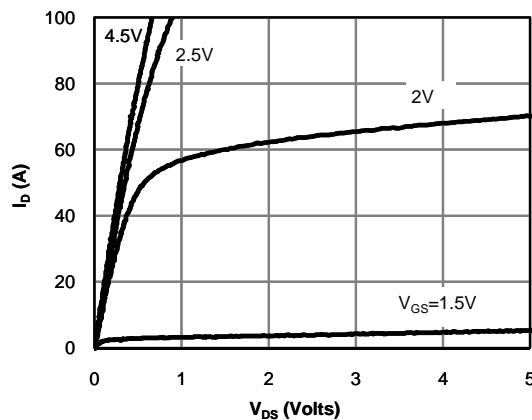
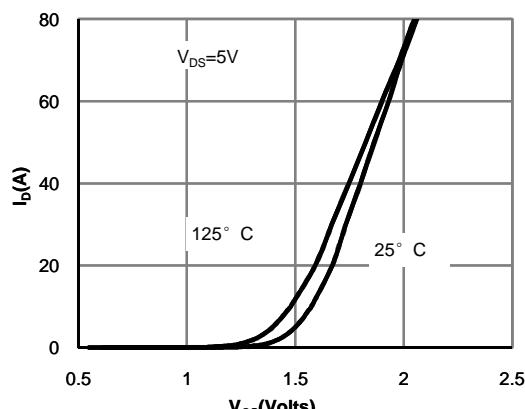
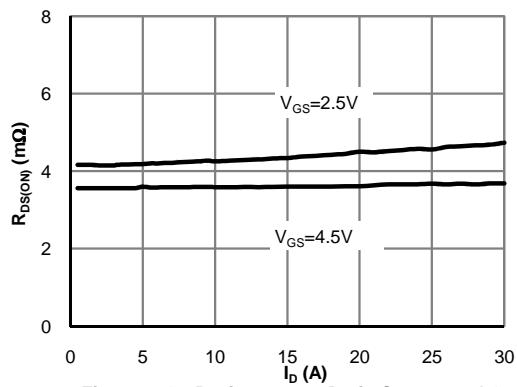
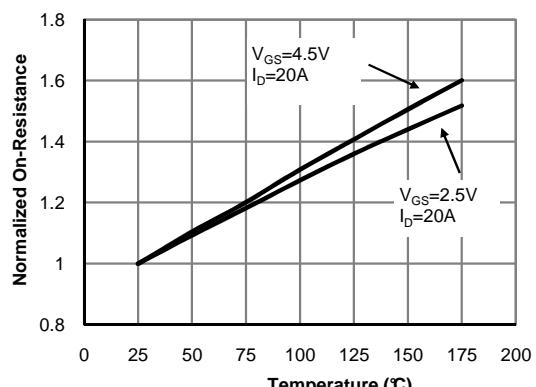
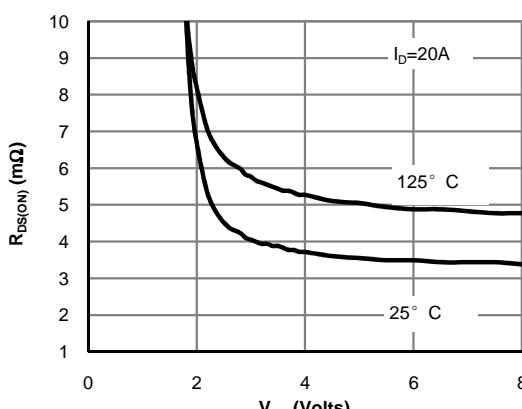
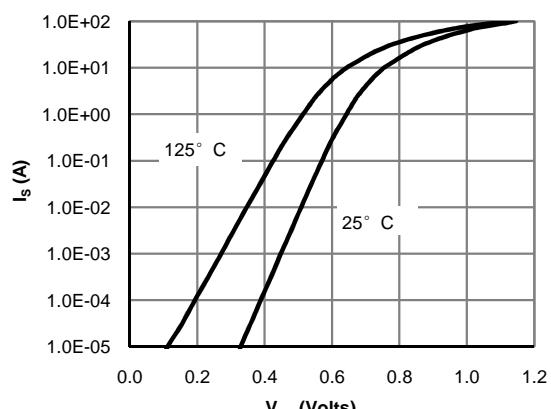
E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

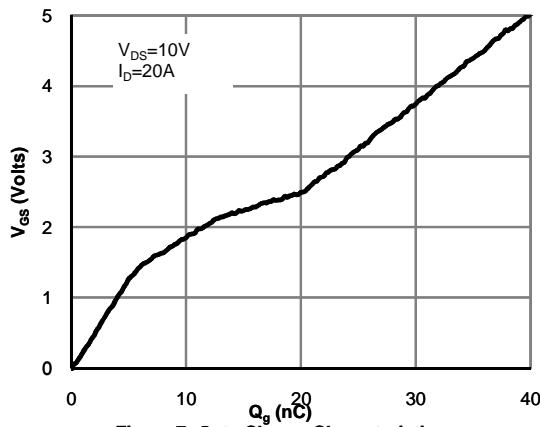
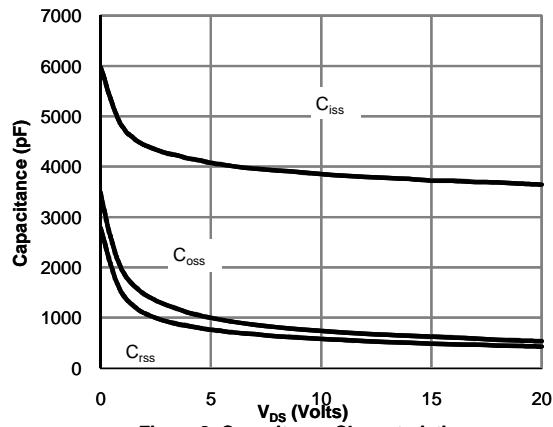
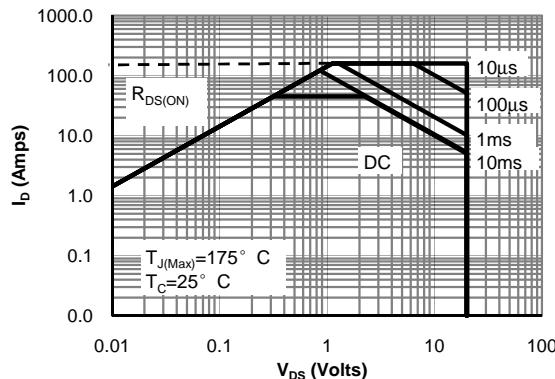
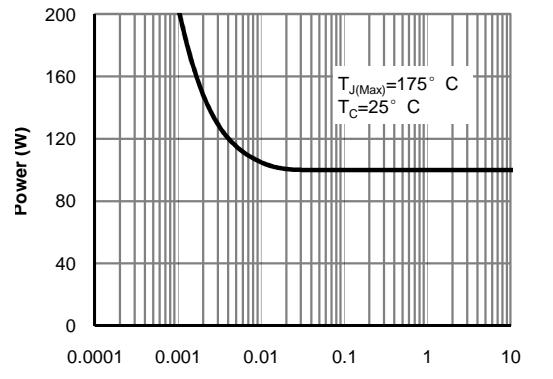
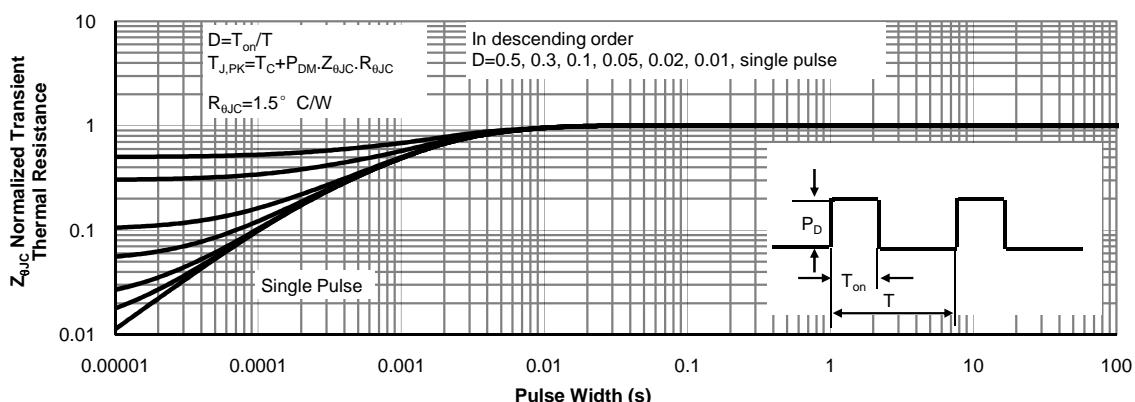
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

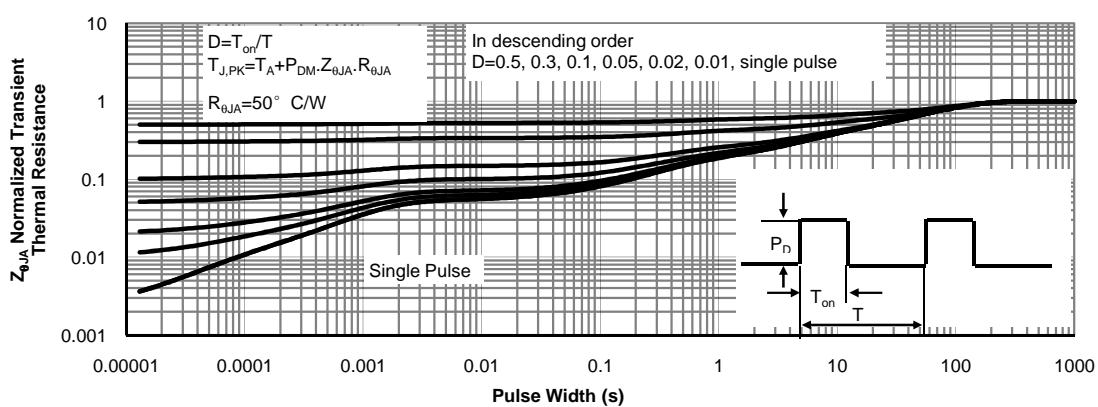
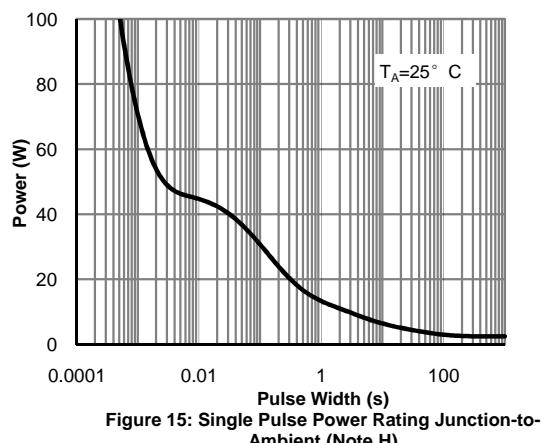
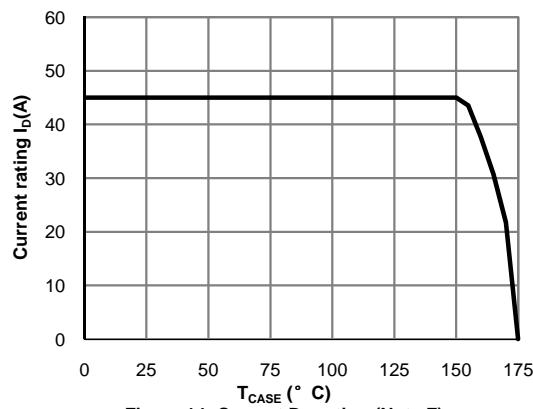
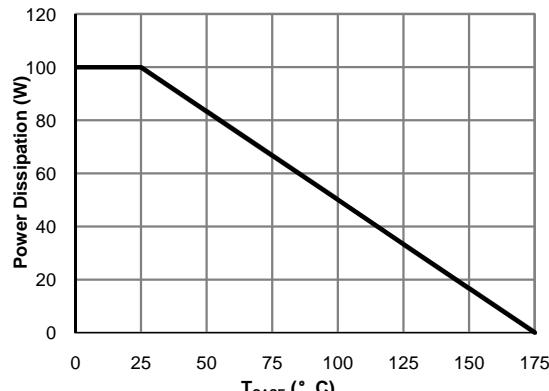
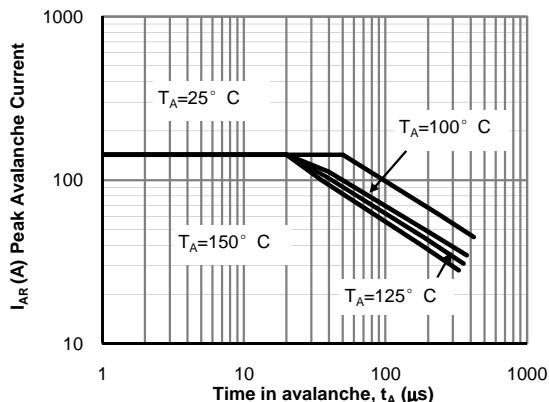
G. The maximum current rating is package limited.

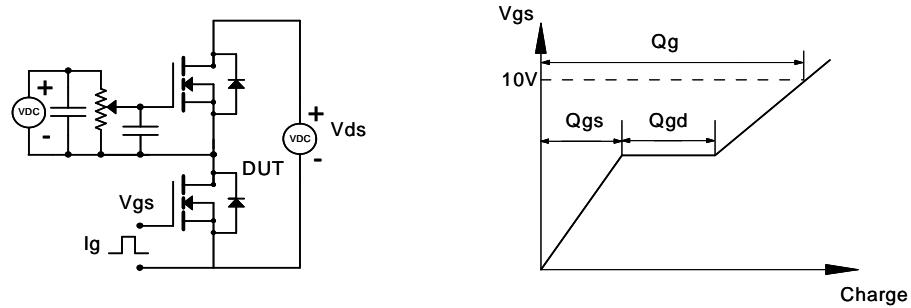
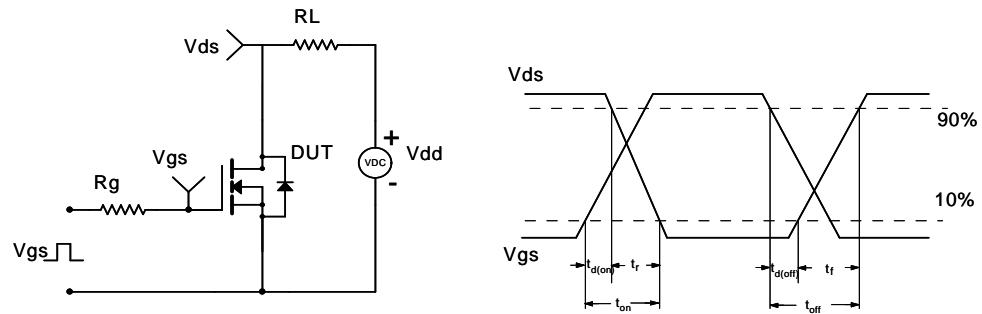
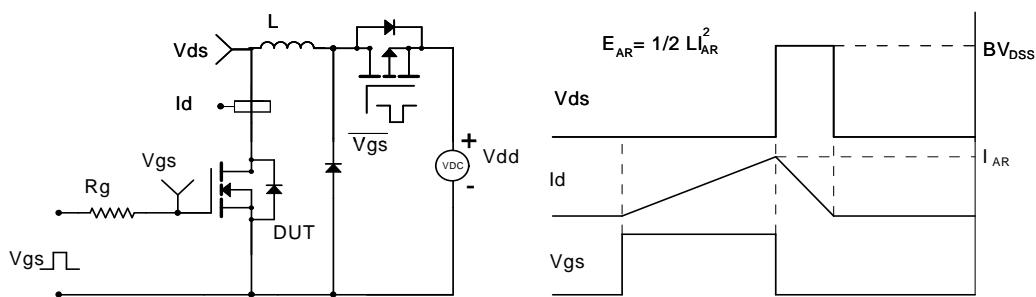
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig 1: On-Region Characteristics (Note E)

Figure 2: Transfer Characteristics (Note E)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

Figure 4: On-Resistance vs. Junction Temperature (Note E)

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

Diode Recovery Test Circuit & Waveforms
